

# HTM2004A-01Y-T5P 12H

产品	名称(Product name)	:	Character Display Modu	ule
型	号(Model)	:	HTM2004A-01Y-T5P	12H
编	号(Part number)	:		
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深圳市鑫洪泰电子科技有限公司 Shenzhen Hot Display Technology Co.,Ltd							
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## 1. Basic Specifications

## 1.1 Display SpecificationsS

1>LCD Display Mode	: STN-YG, Positive, Transflective
2>Viewing Angle	: 12H
3>Driving Method	: 1/16 Duty, 1/5 Bias
4 >Backlight	: Yellow-Green

### **1.2 Mechanical Specifications**

1>Outline Dimension : 98.0 X 60.0 X 10.7mm (See attached Outline Drawing for Data)



#### 1.3 Circuit Diagram





### **1.4 Terminal Function**

Pin No.	Pin Name	Function
1	VSS	Power Supply, (0V)
2	VDD	Positive Power Supply (5.0V)
3	V0	LCD Contrast Reference Supply
4	RS	<ul> <li>Select Register</li> <li>0: Instruction register (for write) busy flag address</li> <li>Counter(for read)</li> <li>1: Data register (for write and read)</li> </ul>
5	R/W	Select read or write 0: Write 1: Read
6	E	Starts data read/write
7	DB0	
8	DB1	
9	DB2	
10	DB3	Data Bus Lines
11	DB4	Data Bus Lilles
12	DB5	
13	DB6	
14	DB7	
15	BLA	Backlight Positive(5.0V)
16	BLK	Backlight Negative(VSS)

## 1.4.1 Display Address

	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18	19	20
Line 1	80	81	82	83	84	85	86	87	88	89	8A	8B	8C	8D	8E	8F	90	91	92	93
Line 2	C0	C1	C2	C3	C4	C5	C6	C7	C8	C9	CA	СВ	сс	CD	CE	CF	D0	D1	D2	D3
Line3	94	95	96	97	98	99	9A	9B	9C	9D	9E	9F	A0	A1	A2	A3	A4	A5	A6	A7
Line4	D4	D5	D6	D7	D8	D9	DA	DB	DC	DE	DF	E0	E1	E2	E3	E4	E5	E6	E7	E8



#### **1.5 Product Outline**





#### 1.6 Schematic Diagram



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## 2. Absolute Maximum Ratings

Items	Symbol	MIN.	MAX.	Unit	Condition
Supply Voltage For Logic	Vdd	-	6.5	V	Vss = 0V
Input Voltage	Vin	VSS	VDD	V	Vss = 0V
Supply Voltage For LCD	VDD-V0	-	6.5	V	-
Operating Temperature	Тор	-20	+70	°C	No Condensation
Storage Temperature	Tst	-30	+80	°C	No Condensation

## **3. Electrical Characteristics**

## 3.1 DC Characteristics

Items	Symbo	MIN.	TYP.	MAX.	Unit	Condition
Supply Voltage For Logic	VDD-VS S	4.5	5.0	5.5	V	
			4.8/5.0		V	<b>Ta= 0/-20</b> ℃
Supply Voltage Fro LCD	VDD-V		4.4		V	Ta= 25℃
	0		4.1/3.9		V	Ta= +50/+70 ℃
Input High Voltage	VIH	2.2		VDD	V	
Input Low Voltage	VIL	0		0.6	V	
Output High Voltage	VOH	2.4			V	
Output Low Voltage	VOL			0.4	V	
Supply Current	IDD		0.2	0.5	mA	VDD=+5V
View Angle (V)	θ	-10		40	deg.	CR≧2
View Angle (H)	ф	-30		30	deg.	CR≧2
Contrast Ratio	CR		5			
Response Time	TON		180	230	mS	
Response Time	TOFF		100	150	mS	

## 3.2 LED Backlight Circuit

Items	Symbol	MIN.	TYP.	MAX.	Unit	Condition
Forword Voltage	Vf BLA	-	5.0	-	V	-
Forword Current	If BLA	-	30	40	mA	-





#### 3.3 AC Characteristics

3.3.1 Write and Read Operation











#### HTM2004A-01Y-T5P 12H

ltem	Symbol	Limit (Min.)	Limit (Max.)	Unit
Enable Cycle Time	tCYCE	1000		ns
Enable Pules Width (High level)	PWEH	450		ns
Enable Rise/Fall Time	tER,tEF		25	ns
Address Set-Up Time ( RS,R/W,E )	tAS	100		ns
Address Hole Time	tAH	10		ns
Data Set-Up Time	tDSW	100		ns
Data Delay Time	tDDR		190	ns
Data Hold Time	tDHR	20		ns

#### 3.3.2 Busy flag check timing



## 4. Function specifications

## 4.1 The Parallel Interface

RS	R/W	Operation							
L	L	Instruction Write operation (MPU writes Instruction code into IR)							
L	H	Read Busy Flag(DB7) and address counter (DB0 ~ DB6)							
H	L	Data Write operation (MPU writes data into DR)							
H	H	Data Read operation (MPU reads data from DR)							



### 4.2 Display Memory Map

## NØ.7066-0T

67-64 63-60	0000	0001	0010	0011	0100	0101	0110	0111	1000	1001	1010	1011	1100	1101	1110	1111
0000	CG RAM (1)										Б	H	••••		2	M
0001	(2)					0	.23	-				9	ш		L	
0010	(3)						Ŀ				æ	6	1.		Ш	
0011	(4)		-					<b>.</b>			H	8	8.1		æ	
0100	(5)						d	ŧ.			3		<b>b</b>	2	ф	
0101	(6)		24				æ				И	ë	39	38.		
0110	ന		8			U	Ŧ	٠.			Ø	*	80	3.	Щ	8,
0111	(8)				6	W	-				.11	3	93	I		<b>.</b>
1000	(1)					Ж	ŀ	28			Π	И	-			
1001	(2)				I	¥		•			Ņ,	ŭ	-	•		
1010	(3)			**		2	.1	Z			ф	К		4	÷	
1011	(4)				ĸ	L		10				.71	**		<b>.</b>	
1100	(5)					\$.	1	12			Ш	M	14	Ħ		24
1101	(6)						121				1.	-	ċ.	8		8
1110	(7)						1.1	4			61	П				4
1111	(8)				0		Ø	æ			3	T	£		C	



### 4.3 Display Commands

#### Instruction Table:

nstruction Tab				Inst	ructi	ion (	Code					Description
Instruction	RS	R/W	DB7	DB6	DB5	DB4	DB3	DB2	DB1	DB0	Description	Time (270KHz)
Clear Display	0	0	0	0	0	0	0	0	0	1	Write "20H" to DDRAM. and set DDRAM address to "00H" from AC	1.52 ms
Return Home	0	0	0	0	0	0	0	0	1	×	Set DDRAM address to "00H" from AC and return cursor to its original position if shifted. The contents of DDRAM are not changed.	1.52 ms
Entry Mode Set	0	0	0	0	0	0	0	1	I/D	s	Sets cursor move direction and specifies display shift. These operations are performed during data write and read.	37 us
Display ON/OFF	0	0	0	0	0	0	1	D	с	в	D=1:entire display on C=1:cursor on B=1:cursor position on	37 us
Cursor or Display Shift	0	0	0	0	0	1	S/C	R/L	×	×	Set cursor moving and display shift control bit, and the direction, without changing DDRAM data.	37 us
Function Set	0	0	0	0	1	DL	N	F	×	×	DL:interface data is 8/4 bits N:number of line is 2/1 F:font size is 5x11/5x8	37 us
Set CGRAM address	0	0	0	1	AC5	AC4	AC3	AC2	AC1	AC0	Set CGRAM address in address counter	37 us
Set DDRAM address	0	0	1	AC6	AC5	AC4	AC3	AC2	AC1	AC0	Set DDRAM address in address counter	37 us
Read Busy flag and address	0	1	BF	AC6	AC5	AC4	AC3	AC2	AC1	AC0	Whether during internal operation or not can be known by reading BF. The contents of address counter can also be read.	0 us
Write data to RAM	1	0	D7	D6	D5	D4	D3	D2	D1	DO	Write data into internal RAM (DDRAM/CGRAM)	37 us
Read data from RAM	1	1	D7	D6	D5	D4	D3	D2	D1	D0	Read data from internal RAM (DDRAM/CGRAM)	37 us

#### Note:

Be sure the ST7066U is not in the busy state (BF = 0) before sending an instruction from the MPU to the ST7066U. If an instruction is sent without checking the busy flag, the time between the first instruction and next instruction will take much longer than the instruction time itself. Refer to Instruction Table for the list of each instruction execution time.



## Instruction Description

#### Clear Display

RS RW DB7 DB6 DB5 DB4 DB3 DB2 DB1 DB0

Code	0	0	0	0	0	0	0	0	0	1
------	---	---	---	---	---	---	---	---	---	---

Clear all the display data by writing "20H" (space code) to all DDRAM address, and set DDRAM address to "00H" into AC (address counter). Return cursor to the original status, namely, bring the cursor to the left edge on first line of the display. Make entry mode increment (I/D = "1").

#### Return Home

RS RW DB7 DB6 DB5 DB4 DB3 DB2 DB1 DB0

		_	_			_				_
Code	0	0	0	0	0	0	0	0	1	x

Return Home is cursor return home instruction. Set DDRAM address to "00H" into the address counter. Return cursor to its original site and return display to its original status, if shifted. Contents of DDRAM does not change.

#### Entry Mode Set

RS RW DB7 DB6 DB5 DB4 DB3 DB2 DB1 DB0

Code	0	0	0	0	0	0	0	1	I/D	S
------	---	---	---	---	---	---	---	---	-----	---

Set the moving direction of cursor and display.

#### I/D : Increment / decrement of DDRAM address (cursor or blink)

When I/D = "High", cursor/blink moves to right and DDRAM address is increased by 1.

When I/D = "Low", cursor/blink moves to left and DDRAM address is decreased by 1.

\* CGRAM operates the same as DDRAM, when read from or write to CGRAM.

#### S: Shift of entire display

When DDRAM read (CGRAM read/write) operation or S = "Low", shift of entire display is not performed. If

S = "High" and DDRAM write operation, shift of entire display is performed according to I/D value (I/D =

"1" : shift left, I/D = "0" : shift right).

S	I/D	Description
H	н	Shift the display to the left
Н	L	Shift the display to the right



#### Display ON/OFF

RS RW DB7 DB6 DB5 DB4 DB3 DB2 DB1 DB0

Code	0	0	0	0	0	0	1	D	С	в
------	---	---	---	---	---	---	---	---	---	---

Control display/cursor/blink ON/OFF 1 bit register.

#### D : Display ON/OFF control bit

When D = "High", entire display is turned on.

When D = "Low", display is turned off, but display data is remained in DDRAM.

### C : Cursor ON/OFF control bit

When C = "High", cursor is turned on.

When C = "Low", cursor is disappeared in current display, but I/D register remains its data.

#### B : Cursor Blink ON/OFF control bit

When B = "High", cursor blink is on, that performs alternate between all the high data and display

character at the cursor position.

When B = "Low", blink is off.

#### Cursor or Display Shift

RS RW DB7 DB6 DB5 DB4 DB3 DB2 DB1 DB0

Code	0	0	0	0	0	1	S/C	R/L	×	x
------	---	---	---	---	---	---	-----	-----	---	---

Without writing or reading of display data, shift right/left cursor position or display. This instruction is used to correct or search display data. During 2-line mode display, cursor moves to the 2nd line after 40th digit of 1st line. Note that display shift is performed simultaneously in all the line. When displayed data is shifted repeatedly, each line shifted individually. When display shift is performed, the contents of address counter are not changed.

S/C	R/L	Description	AC Value
L	L	Shift cursor to the left	AC=AC-1
L	Н	Shift cursor to the right	AC=AC+1
Н	Ľ	Shift display to the left. Cursor follows the display shift	AC=AC
н	Н	Shift display to the right. Cursor follows the display shift	AC=AC

#### Function Set

RS RW DB7 DB6 DB5 DB4 DB3 DB2 DB1 DB0

Code	0	0	0	0	1	DL	N	F	×	x
------	---	---	---	---	---	----	---	---	---	---



#### > DL : Interface data length control bit

When DL = "High", it means 8-bit bus mode with MPU.

When DL = "Low", it means 4-bit bus mode with MPU. So to speak, DL is a signal to select

8-bit or 4-bit bus mode.

When 4-bit bus mode, it needs to transfer 4-bit data by two times.

#### N : Display line number control bit

When N = "Low", it means 1-line display mode.

When N = "High", 2-line display mode is set.

#### F : Display font type control bit

When F = "Low", it means 5 x 8 dots format display mode

When F = "High", 5 x11 dots format display mode.

N	F	No. of Display Lines	<b>Character Font</b>	<b>Duty Factor</b>
L	L	1	5x8	1/8
L	н	1	5x11	1/11
Н	x	2	5x8	1/16

Set CGRAM Address

	RS	RW	DB7	DB6	DB5	DB4	DB3	DB2	DB1	DB0
Code	0	0	0	1	AC5	AC4	AC3	AC2	AC1	AC0

#### Set CGRAM address to AC.

This instruction makes CGRAM data available from MPU.

#### Set DDRAM Address

RS RW DB7 DB6 DB5 DB4 DB3 DB2 DB1 DB0

de	0	0	1	AC6	AC5	AC4	AC3	AC2	AC1	AC0
----	---	---	---	-----	-----	-----	-----	-----	-----	-----

Set DDRAM address to AC.

This instruction makes DDRAM data available from MPU.

When 1-line display mode (N = 0), DDRAM address is from "00H" to "4FH".

In 2-line display mode (N = 1), DDRAM address in the 1st line is from "00H" to "27H", and

DDRAM address in the 2nd line is from "40H" to "67H".



Read Busy Flag an	Address					
	nu Audicaa					
	RS RW D	B7 DB6 DB5 D	B4 DB3 DB2	DB1 DB0		
Coc		BF AC6 AC5 A	C4 AC3 AC2	AC1 AC0		
When BF = "High"	" indicates that	t the internal on	eration is bein	a processe	So during this	time the next
instruction cannot		the memory op		ig processes	.co during the	and the next
The address Cour	an and the second second second	s DDRAM/CGR	AM addresse	s transferre	d from IR	
After writing into (	and the second second					ed) by 1.
Write Data to CGR						
		DB7 DB6 DB5 DB	4 DB3 DB2 DB1	DB0		
	Code 1 0	D7 D6 D5 D4		a deste		
		07 00 05 04	03 02 01	00		
Vrite hinen: 9 hit dat		CRAM				
Vrite binary 8-bit dat The selection of RAM			t by the provid	aus addross	a of instruction	
DDRAM address se						
irection to RAM.	r, CORAM aut	iless set. MAIN	set instruction	can also de	termine the AC	
After write operation	the address is	automatically in	ncreased/decr	eased by 1	according to	
Second Second	the address is	automatically in	ncreased/decr	eased by 1,	according to	
ne entry mode.			ncreased/decr	eased by 1,	according to	
and the second			ncreased/decr	eased by 1,	according to	
he entry mode.	GRAM or DDR			0	according to	
ne entry mode.	GRAM or DDR	AM DB7 DB6 DB5 DB		DB0	according to	
ne entry mode.	GRAM or DDR	AM DB7 DB6 DB5 DB	4 DB3 DB2 DB1	DB0	according to	
e entry mode. Read Data from Co	GRAM or DDR RS RW Code 1 1	AM DB7 DB6 DB5 DB D7 D6 D5 D4	4 DB3 DB2 DB1	DB0	according to	
ne entry mode. Read Data from Co Read binary 8-bit dat	GRAM or DDR RS RW Code 1 1	AM DB7 DB6 DB5 DB D7 D6 D5 D4 M/CGRAM.	4 DB3 DB2 DB1 4 D3 D2 D1	DB0 D0		n of RAM is not
ne entry mode. Read Data from Co Read binary 8-bit dat The selection of RAM	GRAM or DDR RS RW Code 1 1 a from DDRAM I is set by the p	DB7 DB6 DB5 DB D7 D6 D5 D4 M/CGRAM.	4 DB3 DB2 DB1 1 D3 D2 D1 ss set instructi	DB0 D0 on. If addres	s set instruction	
he entry mode. Read Data from Co Read binary 8-bit dat The selection of RAM performed before th	GRAM or DDR RS RW Code 1 1 a from DDRAM I is set by the p is instruction,	DB7 DB6 DB5 DB D7 D6 D5 D4 M/CGRAM. previous addres the data that r	4 DB3 DB2 DB1 1 D3 D2 D1 as set instructions in the set instruction in the set instruction is in the set in	DB0 D0 on. If addres valid, becau	s set instruction	n of AC is not
After write operation, he entry mode. <b>Read Data from Co</b> Read binary 8-bit dat The selection of RAM performed before the determined. If you reav you can get correct R	GRAM or DDR RS RW Code 1 1 a from DDRAM I is set by the p is instruction, ad RAM data s	AM DB7 DB6 DB5 DB D7 D6 D5 D4 M/CGRAM. previous address the data that reveral times with	4 DB3 DB2 DB1 1 D3 D2 D1 as set instructions in thout RAM additional content of the set of the se	DB0 D0 on. If addres valid, becau dress set ins	s set instruction se the direction struction before	n of AC is not read operation,
Read Data from Co Read Data from Co Read binary 8-bit dat The selection of RAM erformed before the letermined. If you read ou can get correct R	GRAM or DDR RS RW Code 1 1 a from DDRAM I is set by the p is instruction, ad RAM data s AM data from t	AM DB7 DB6 DB5 DB D7 D6 D5 D4 M/CGRAM. previous address the data that reveral times with	4 DB3 DB2 DB1 1 D3 D2 D1 as set instructions in thout RAM additional content of the set of the se	DB0 D0 on. If addres valid, becau dress set ins	s set instruction se the direction struction before	n of AC is not read operation,
Read Data from Co Read Data from Co Read binary 8-bit dat the selection of RAM performed before the letermined. If you read ou can get correct R margin to transfer RA	GRAM or DDR RS RW Code 1 1 a from DDRAM I is set by the p is instruction, ad RAM data s AM data from 1 M data.	DB7 DB6 DB5 DB D7 D6 D5 D4 M/CGRAM. previous addres the data that r everal times with the second, but	4 DB3 DB2 DB1 D3 D2 D1 ss set instructive ad first is in thout RAM add the first data w	DB0 D0 on. If addres valid, becau dress set ins vould be inco	ss set instruction use the direction struction before prrect, because t	n of AC is not read operation, there is no time
Read Data from Co Read Data from Co Read binary 8-bit dat The selection of RAM performed before the determined. If you rea you can get correct R nargin to transfer RA n case of DDRAM	GRAM or DDR RS RW Code 1 1 a from DDRAM I is set by the p is instruction, ad RAM data s AM data from the M data. read operation	AM DB7 DB6 DB5 DB D7 D6 D5 D4 M/CGRAM. previous address the data that reveral times with the second, but on, cursor shift	4 DB3 DB2 DB1 1 D3 D2 D1 as set instruction thout RAM addition the first data with	DB0 D0 on. If addres valid, becau dress set ins vould be inco	ss set instruction use the direction struction before prrect, because to me role as DE	n of AC is not read operation, there is no time DRAM address
Read Data from Co Read Data from Co Read binary 8-bit dat The selection of RAM performed before the letermined. If you rea tou can get correct R margin to transfer RA n case of DDRAM per instruction : it als	GRAM or DDR RS RW Code 1 1 a from DDRAM A is set by the p is instruction, ad RAM data s AM data from the AM data. read operations to transfer RAM	DB7 DB6 DB5 DB D7 D6 D5 D4 M/CGRAM. orevious addres the data that r everal times with the second, but	4 DB3 DB2 DB1 D3 D2 D1 BS set instruction thout RAM add the first data was t instruction point ut data register	DB0 D0 on. If addres valid, becau dress set ins vould be inco plays the sa	ss set instruction use the direction struction before prrect, because to me role as DE	n of AC is not read operation, there is no time DRAM address ress counter is
Read Data from Co Read Data from Co Read binary 8-bit dat The selection of RAM performed before the letermined. If you rea ou can get correct R nargin to transfer RA n case of DDRAM set instruction : it als nutomatically increas	GRAM or DDR RS RW Code 1 1 a from DDRAM I is set by the p is instruction, ad RAM data s AM data from the AM data. read operations to transfer RAM	DB7 DB6 DB5 DB D7 D6 D5 D4 D7 D6 D5 D4 M/CGRAM. Drevious addres the data that r everal times with the second, but on, cursor shif M data to output by 1 according	4 DB3 DB2 DB1 D3 D2 D1 BS set instruction thout RAM add the first data was t instruction point ut data register	DB0 D0 on. If addres valid, becau dress set ins vould be inco plays the sa	ss set instruction use the direction struction before prrect, because to me role as DE	n of AC is not read operation, there is no time DRAM address ress counter is
he entry mode. Read Data from Co Read binary 8-bit dat The selection of RAM performed before the determined. If you read	GRAM or DDR RS RW Code 1 1 a from DDRAM I is set by the p is instruction, ad RAM data s AM data from the AM data. read operation to transfer RAM read operation to transfer RAM	AM DB7 DB6 DB5 DB D7 D6 D5 D4 M/CGRAM. previous address the data that re- everal times with the second, but on, cursor shift M data to output by 1 according	4 DB3 DB2 DB1 1 D3 D2 D1 as set instruction thout RAM add the first data was t instruction part ut data register to the entry magnetic to the entry	DB0 D0 on. If address valid, becau dress set ins vould be inco oblays the sa er. After reac bode. After C	ss set instruction ise the direction struction before prrect, because to me role as DE d operation add GRAM read op	n of AC is not read operation, there is no time DRAM address ress counter is eration, display



#### 4.4 Basic Operating Sequence



2) 4 Bit Interface



Busy flag is checked after instructions are completed. If busy flay isn't checked, the waiting time between
instructions should be longer than execution time of these instructions.



## 5. Inspection Standards

Item	Criterion for defects	Defect type				
1) Display on inspection	(1) Non display (2) Vertical line is deficient	Major				
, , , , , , , , , , , , , , , , , , , ,	(3) Horizontal line is deficient     (4) Cross line is deficient       Size $\Phi(mm)$ Acceptable number	,				
	$\Phi \leq 0.3$ Ignore (note)					
2) Black / White spot	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$					
	0.6< Φ 0					
	Length (mm) Width (mm) Acceptable number					
	L≤10 W≤0.03 Ignore					
	5.0≤L≤10 0.03 <w≤0.04 3<="" td=""><td></td></w≤0.04>					
3) Black / White line	5.0≤L≤10 0.04 <w≤0.05 2<br="">1.0≤L≤10 0.05<w≤0.06 2<="" td=""><td>Minor</td></w≤0.06></w≤0.05>	Minor				
	1.0≤L≤10 0.05<₩≤0.00 2 1.0≤L≤10 0.06<₩≤0.08 1					
	$L \le 10$ 0.08 <w 2)="" defect<="" follows="" point="" td=""><td></td></w>					
	Defects separate with each other at an interval of more than 20mm					
	· · · · · · · · · · · · · · · · · · ·					
4) Display pattern		Minor				
	<u>A+B</u> ≤0.28  0 <c  <u="">D+E≤0.25  <u>F+G</u>≤0.25</c >					
	$\frac{\underline{110}}{2} = \frac{12}{2} = \frac{12}{2} = \frac{110}{2} = \frac{100}{2} = 1$					
	Note: 1) Up to 3 damages acceptable					
	2) Not allowed if there are two or more pinholes every three-fourth inch.					
	Size $\Phi(mm)$ Acceptable Number					
	$\Phi \leq 0.7$ Ignore (note)					
5) Spot-like contrast	$ \begin{array}{cccccccccccccccccccccccccccccccccccc$					
rregularity	1.5< Φ 0	Minor				
	Note: 1) Conformed to limit samples.					
	2) Intervals of defects are more than 30mm.					
	Size $\Phi(mm)$ Acceptable Number					
6) Bubbles in polarizer	$ \begin{array}{c cccc} & & & & & & & & \\ & & & & & & \\ & & & & & & \\ & & & & & & & \\ & & & & & & & \\ & & & & & & & & \\ & & & & & & & & \\ & & & & & & & & \\ & & & & & & & & \\ & & & & & & & & \\ & & & & & & & & \\ & & & & & & & & \\ & & & & & & & & \\ & & & & & & & & \\ & & & & & & & & \\ & & & & & & & & \\ & & & & & & & & \\ & & & & & & & & \\ & & & & & & & & \\ & & & & & & & & \\ & & & & & & & & \\ & & & & & & & & \\ & & & & & & & & \\ & & & & & & & \\ & & & & & & & \\ & & & & & & & \\ & & & & & & & \\ & & & & & & & \\ & & & & & & & \\ & & & & & \\ & & & & & &$					
7) Scratches and dent on the polarizer	Scratches and dent on the polarizer shall be in the accordance with "2) Black/white spot", and "3) Black/White line".	Minor				
8) Stains on the surface of LCD panel	Stains which cannot be removed even when wiped lightly with a soft cloth or similar cleaning.	Minor				
9) Rainbow color	No rainbow color is allowed in the optimum contrast on state within the active	Minor				
10) Viewing area	area. Polarizer edge or line is visible in the opening viewing area due to polarizer	Minor				
encroachment 11) Bezel appearance	shortness or sealing line. Rust and deep damages that are visible in the bezel are rejected.	Minor				
12) Defect of land surface						
<sup>′</sup> contact	Evident crevices that are visible are rejected.	Minor				
	(1) Failure to mount parts	Minor				
13) Parts mounting	<ul><li>(2) Parts not in the specifications are mounted</li><li>(3) For example: Polarity is reversed, HSC or TCP falls off.</li></ul>	Minor				
	<ul> <li>(1) LSI, IC lead width is more than 50% beyond pad outline.</li> </ul>					
14) Part alignment	<ul> <li>(1) Lot, to lead width is more than 50% beyond pad outline.</li> <li>(2) More than 50% of LSI, IC leads is off the pad outline.</li> </ul>	Minor				
15) Conductive foreign	(1) 0.45<Φ, N≥1					
matter (solder ball,	(2) $0.3 < \Phi \le 0.45$ , N $\ge 1$ , $\Phi$ : Average diameter of solder ball (unit: mm)	Minor				
solder hips)	(3) 0.5 <l, (unit:="" average="" chip="" l:="" length="" mm)<="" n≥1,="" of="" solder="" td=""><td></td></l,>					
16) Bezel flaw	Bezel claw missing or not bent	Minor				
17) Indication on name plate	<ol> <li>Failure to stamp or label error, or not legible.(all acceptable if legible)</li> <li>The congration is more than 1/3 for indication discoloration in which the</li> </ol>	Minor				
(sampling indication label)	(2) The separation is more than 1/3 for indication discoloration, in which the	IVITIO				



## 6. Handling Precautions

#### 6.1 Mounting method

A panel of LCD module made by our company consists of two thin glass plates with polarizers that easily get damaged. And since the module in so constructed as to be fixed by utilizing fitting holes in the printed circuit board (PCB), extreme care should be used when handling the LCD modules.

#### 6.2 Cautions of LCD handling and cleaning

When cleaning the display surface, use soft cloth with solvent (recommended below) and wipe lightly.

-Isopropyl alcohol

-Ethyl alcohol

-Trichlorotriflorothane

Do not wipe the display surface with dry or hard materials that will damage the polarizer surface.

Do not use the following solvent:

-Water

-Ketene

-Aromatics

#### 6.3 Caution against static charge

The LCD module use C-MOS LSI drivers. So we recommend you:

Connect any unused input terminal to  $V_{dd}$  or  $V_{ss}$ . Do not input any signals before power is turned on, and ground your body, work/assembly areas, assembly equipment to protect against static electricity.

#### 6.4 Packaging

-Module employs LCD elements, and must be treated as such. Avoid intense shock and falls from a height. -To prevent modules from degradation, do not operate or store them exposed direct to sunshine or high temperature/humidity.

#### 6.5 Caution for operation

-It is an indispensable condition to drive LCD module within the limits of the specified voltage since the higher voltage over the limits may cause the shorter life of LCD module.

-An electrochemical reaction due to DC (direct current) causes LCD undesirable deterioration so that the uses of DC (direct current) drive should be avoided.

-Response time will be extremely delayed at lower temperature than the operating temperature range and on the other hand at higher temperature LCD module may show dark color in them. However those phenomena do not mean malfunction or out of order of LCD module, which will come back in the specified operating temperature.

#### 6.6 Storage

In the case of storing for a long period of time, the following ways are recommended:

-Storage in polyethylene bag with the opening sealed so as not to enter fresh air outside in it. And with not desiccant.

-Placing in a dark place where neither exposure to direct sunlight nor light is. Keeping the storage temperature range. -Storing with no touch on polarizer surface by any thing else.

#### 6.7 Safety

-It is recommendable to crash damaged or unnecessary LCD into pieces and to wash off liquid crystal by either of solvents such as acetone and ethanol, which should be burned up later.

-When any liquid leaked out of a damaged glass cell comes in contact with your hands, please wash it off well at once with soap and water.